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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	64
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 17x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LFQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104mgdfb-x0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

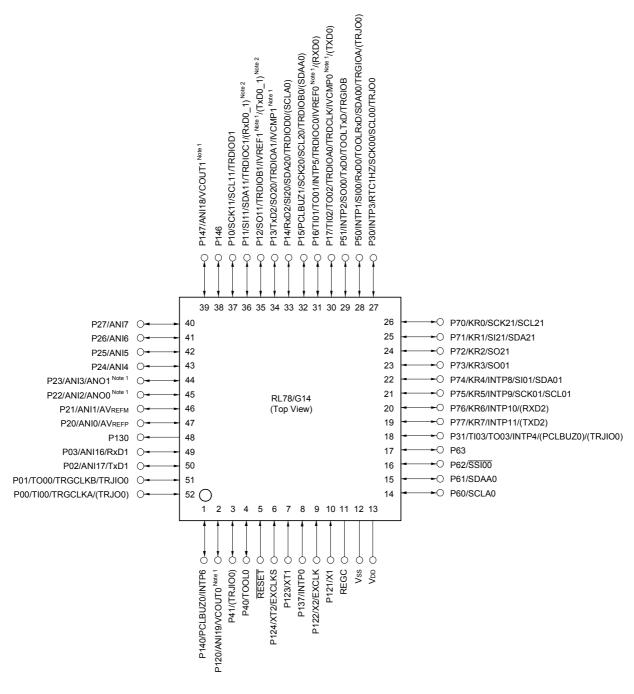
1.3.6 48-pin products

• 48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch) P01/T000/RxD1/TRGCLKB/TRJI00 P00/T100/TxD1/TRGCLKA/(TRJO0) P140/PCLBUZ0/INTP6 P22/ANI2/ANO0 Note P23/ANI3/ANO1 Note P21/ANI1/AVREFM P24/ANI4 P130 36 35 34 33 32 31 30 29 28 27 26 25 120/ANI19/VCOUT0 Note 1 24 P147/ANI18/VCOUT1 Note 1 P41/(TRJIO0) 23 38 P146 P40/TOOL0 O 22 39 P10/SCK11/SCL11/TRDIOD1 RESET 40 21 P11/SI11/SDA11/TRDIOC1/(RxD0_1) Note 2 P124/XT2/EXCLKS 20 41 P12/SO11/TRDIOB1/IVREF1 Note 1 /(TxD0_1) Note 2 P123/XT1 42 RL78/G14 19 P13/TxD2/SO20/TRDIOA1/IVCMP1 Note 1 (Top View) P137/INTP0 18 43 P122/X2/EXCLK O 17 44 P15/PCLBUZ1/SCK20/SCL20/TRDIOB0/(SDAA0) P121/X1 16 \circ 45 P16/TI01/TO01/INTP5/TRDIOC0/IVREF0 Note 1/(RXD0) REGC 0 46 15 P17/TI02/TO02/TRDIOA0/TRDCLK/IVCMP0 Note 1/(TXD0) **-**○ Vss 47 14 P51/INTP2/SO00/TxD0/TOOLTxD/TRGIOB V_{DD} \bigcirc 48 13 P50/INTP1/SI00/RxD0/TOOLRxD/SDA00/TRGIOA/(TRJO0 8 9 10 11 12 P60/SCLA0 P61/SDAA0 P62/SS100 P74/KR4/INTP8/SI01/SDA01 P30/INTP3/RTC1HZ/SCK00/SCL00/TRJO0 P31/TI03/T003/INTP4/(PCLBUZ0)/(TRJI00) P72/KR2/S021 P75/KR5/INTP9/SCK01/SCL01 P73/KR3/S001 P71/KR1/SI21/SDA21 P70/KR0/SCK21/SCL21

- **Note 1.** Mounted on the 96 KB or more code flash memory products.
- Note 2. Mounted on the 384 KB or more code flash memory products.
- Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

1.3.7 52-pin products

• 52-pin plastic LQFP (10 × 10 mm, 0.65 mm pitch)



Note 1. Mounted on the 96 KB or more code flash memory products.

Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

Note

The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F104xJ (x = F, G, J, L, M, P): Start address F9F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.



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					(2/2)				
		44-pin	48-pin	52-pin	64-pin				
	Item	R5F104Fx	R5F104Gx	R5F104Jx	R5F104Lx				
		(x = F to H, J)	(x = F to H, J)	(x = F to H, J)	(x = F to H, J)				
Clock output/buz	zer output	2	2	2	2				
		(Main system clock: • 256 Hz, 512 Hz, 1.02	fmain = 20 MHz operation	96 kHz, 8.192 kHz, 16.3					
8/10-bit resolutio	n A/D converter	10 channels	10 channels	12 channels	12 channels				
D/A converter		2 channels		ı	1				
Comparator		2 channels							
Serial interface	120 1	CSI: 1 channel/UAR CSI: 2 channels/UAF [48-pin, 52-pin product CSI: 2 channels/UAF CSI: 1 channel/UAR CSI: 2 channels/UAF	T: 1 channel/simplified I RT: 1 channel/simplified I ts] RT (UART supporting LI T: 1 channel/simplified I RT: 1 channel/simplified RT (UART supporting LI RT: 1 channel/simplified	I ² C: 2 channels IN-bus): 1 channel/simp ² C: 1 channel I ² C: 2 channels IN-bus): 1 channel/simp I ² C: 2 channels I ² C: 2 channels	olified I ² C: 2 channels olified I ² C: 2 channels				
	I ² C bus	1 channel	1 channel	1 channel	1 channel				
Data transfer cor	troller (DTC)	31 sources	s 32 sources 33 sources						
Event link contro	ller (ELC)	Event input: 22 Event trigger output: 9							
Vectored inter-	Internal	24	24	24	24				
rupt sources	External	7	10	12	13				
Key interrupt	1	4	6	8	8				
Power-on-reset of	circuit	 Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note Internal reset by RAM parity error Internal reset by illegal-memory access Power-on-reset: 1.51 ±0.04 V (TA = -40 to +85°C) 1.51 ±0.06 V (TA = -40 to +105°C) Power-down-reset: 1.50 ±0.04 V (TA = -40 to +85°C) 							
Voltage detector		1.63 V to 4.06 V (14 s	1.50 ±0.06 V (TA = -40 to +105°C)						
On-chip debug fu	ınction	Provided							
Power supply vol		VDD = 1.6 to 5.5 V (TA = -40 to +85°C) VDD = 2.4 to 5.5 V (TA = -40 to +105°C)							
Operating ambie	nt temperature		Consumer applications, : Industrial applications	, D: Industrial applicatio)	ns),				

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

[80-pin, 100-pin products (code flash memory 96 KB to 256 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

		80-pin	100-pin					
	Item	R5F104Mx	R5F104Px					
		(x = F to H, J)	(x = F to H, J)					
Code flash me	emory (KB)	96 to 256	96 to 256					
Data flash me	mory (KB)	8	8					
RAM (KB)		12 to 24 ^{Note} 12 to 24 ^{Note}						
Address space	e	1 MB						
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)						
	High-speed on-chip oscillator clock (fін)	HS (high-speed main) mode: 1 to 32 MHz (V HS (high-speed main) mode: 1 to 16 MHz (V LS (low-speed main) mode: 1 to 8 MHz (VD LV (low-voltage main) mode: 1 to 4 MHz (VD	DD = 2.4 to 5.5 V), D = 1.8 to 5.5 V),					
Subsystem clo	ock	XT1 (crystal) oscillation, external subsystem of	lock input (EXCLKS) 32.768 kHz					
Low-speed on	n-chip oscillator clock	15 kHz (TYP.): VDD = 1.6 to 5.5 V						
General-purpo	ose register	8 bits × 32 registers (8 bits × 8 registers × 4 banks)						
Minimum instr	ruction execution time	0.03125 μs (High-speed on-chip oscillator clock: fiн = 32 MHz operation)						
		0.05 μs (High-speed system clock: fмx = 20 M	IHz operation)					
		30.5 μs (Subsystem clock: fsub = 32.768 kHz	operation)					
Instruction set	t	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bit Multiplication and Accumulation (16 bits × 16 bits + 32 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 						
I/O port	Total	74	92					
	CMOS I/O	64	82					
	CMOS input	5	5					
	CMOS output	1	1					
	N-ch open-drain I/O (6 V tolerance)	4	4					
Timer	16-bit timer	12 channels (TAU: 8 channels, Timer RJ: 1 channel, Timer	RD: 2 channels, Timer RG: 1 channel)					
	Watchdog timer	1 channel						
	Real-time clock (RTC)	1 channel						
	12-bit interval timer	1 channel						
	Timer output	Timer outputs: 18 channels PWM outputs: 12 channels						
	RTC output	1 • 1 Hz (subsystem clock: fsub = 32.768 kHz)						

Note

In the case of the 24 KB, this is about 23 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/G14 User's Manual).

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

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Items	Symbol	Conditions	3	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0.8 EVDD0		EV _{DD0}	V
	VIH2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55,	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	2.2		EV _{DD0}	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	2.0		EV _{DD0}	V
			TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	1.5		EV _{DD0}	V
	VIH3	P20 to P27, P150 to P156	0.7 Vdd		VDD	V	
	VIH4	P60 to P63	0.7 EVDD0		6.0	V	
	VIH5	P121 to P124, P137, EXCLK, EX	CLKS, RESET	0.8 Vdd		VDD	V
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0		0.2 EVDD0	V
	VIL2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55,	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	0		0.8	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	0		0.32	V
	VIL3	P20 to P27, P150 to P156	1	0		0.3 VDD	V
	VIL4	P60 to P63		0		0.3 EVDD0	V
	VIL5	P121 to P124, P137, EXCLK, EX	CLKS, RESET	0		0.2 Vdd	V

Caution The maximum value of ViH of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 is EVDD0, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator).

 The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- Note 8. Current flowing during programming of the data flash.
- Note 9. Current flowing during self-programming.
- Note 10. For shift time to the SNOOZE mode, see 23.3.3 SNOOZE mode in the RL78/G14 User's Manual.
- **Note 11.** Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IDAC when the D/A converter operates in an operation mode or the HALT mode.
- Note 12. Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2, or IDD3 and ICMP when the comparator circuit is in operation.
- Note 13. A comparator and D/A converter are provided in products with 96 KB or more code flash memory.
- Remark 1. fil: Low-speed on-chip oscillator clock frequency
- Remark 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 3. fclk: CPU/peripheral hardware clock frequency
- Remark 4. Temperature condition of the TYP. value is TA = 25°C

(5) During communication at same potential (simplified I²C mode)

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

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Parameter	Symbol	Conditions	HS (high-speed mode	main)	LS (low-speed m	nain)	LV (low-voltage r mode	main)	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu: dat	$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	1/fmcK + 85 Note 2		1/fmck + 145 Note 2		1/fmck + 145 Note 2		ns
		1.8 V \leq EV _{DD0} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1/fmck + 145 Note 2		1/fmck + 145 Note 2		1/fmck + 145 Note 2		ns
		$1.8~V \leq EV_{DD0} < 2.7~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1/fmck + 230 Note 2		1/fmck + 230 Note 2		1/fmck + 230 Note 2		ns
		$1.7~V \leq EV_{DD0} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1/fmck + 290 Note 2		1/fmck + 290 Note 2		1/fmck + 290 Note 2		ns
		$1.6 \ V \le EV_{DD0} < 1.8 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$	_		1/fmck + 290 Note 2		1/fmck + 290 Note 2		ns
Data hold time (transmission)	thd: dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	0	305	0	305	0	305	ns
		1.8 V \leq EV _{DD0} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ	0	355	0	355	0	355	ns
		$1.8~V \leq EV_{DD0} < 2.7~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	0	405	0	405	0	405	ns
		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	0	405	0	405	0	405	ns
		$1.6 \ V \leq EV_{DD0} < 1.8 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$	_		0	405	0	405	ns

Note 1. The value must also be equal to or less than fmck/4.

Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

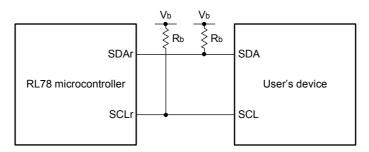
(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(TA = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

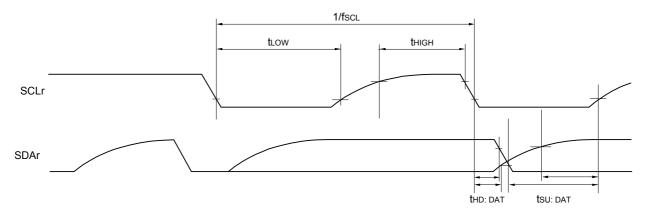
Parameter	Parameter Symbol		nditions	, ,	h-speed mode		r-speed mode		-voltage mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkCY2	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$	24 MHz < fmck	14/fмск		_		_		ns
Note 1		$2.7~V \leq V_b \leq 4.0~V$	20 MHz < fмcк ≤ 24 MHz	12/fмск		_		_		ns
			8 MHz < fмcк ≤ 20 MHz	10/fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/fмск		_		ns
			fмcк ≤ 4 MHz	6/fмск		10/fмск		10/fмск		ns
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V $	24 MHz < fmck	20/fмск		_		_		ns
			20 MHz < fмcк ≤ 24 MHz	16/fмск		_		_		ns
			16 MHz < fмcк ≤ 20 MHz	14/fмск		_		_		ns
			8 MHz < fмcк ≤ 16 MHz	12/fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/fмск		_		ns
			fмcк ≤ 4 MHz	6/fмск		10/fмск		10/fмск		ns
		1.8 V ≤ EVDD0 < 3.3 V,	24 MHz < fmck	48/fмск		_		_		ns
		$1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V}$ Note 2	20 MHz < fмcк ≤ 24 MHz	36/fмск		_		_		ns
			16 MHz < fмcк ≤ 20 MHz	32/fмск		_		_		ns
			8 MHz < fмcк ≤ 16 MHz	26/fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		16/fмск		_		ns
			fмcк ≤ 4 MHz	10/fмск		10/fмск		10/fмск		ns
SCKp high-/ low-level width	tĸH2, tĸL2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2	2.7 V ≤ V _b ≤ 4.0 V	tксү2/2 - 12		tkcy2/2 - 50		tксү2/2 - 50		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2	$2.3~V \leq V_b \leq 2.7~V$	tксү2/2 - 18		tkcy2/2 - 50		tксү2/2 - 50		ns
		1.8 V ≤ EVDD0 < 3.3 V,	$1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V Note 2}$	tксү2/2 - 50		tkcy2/2 - 50		tксү2/2 - 50		ns
SIp setup time (to SCKp↑) Note 3	tsık2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2	$2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$		1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		1.8 V ≤ EVDD0 < 3.3 V,	$1.6~\text{V} \leq \text{V}_\text{b} \leq 2.0~\text{V}~\text{Note}~2$	1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
SIp hold time (from SCKp↑) Note 4	tksi2			1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓ to SOp	tkso2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, \Omega$ Cb = 30 pF, Rb = 1.4 k Ω			2/fмск + 120		2/fмск + 573		2/fмск + 573	ns
output Note 5		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \Omega$ Cb = 30 pF, Rb = 2.7 k Ω			2/fмск + 214		2/fмск + 573		2/fмск + 573	ns
		1.8 V ≤ EV _{DD0} < 3.3 V, C _b = 30 pF, Rv = 5.5 kΩ	$1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V} \text{ Note 2},$		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns

 $(\textbf{Notes},\,\textbf{Caution},\, \text{and}\,\, \textbf{Remarks}$ are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remark 1. $Rb[\Omega]$: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 01, 10, 11, 20, 30, 31), g: PIM, POM number (g = 0, 1, 3 to 5, 14)

Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),

n: Channel number (n = 0, 2), mn = 00, 01, 02, 10, 12, 13)

(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI14, ANI16 to ANI20, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V		1.2	±7.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3		1.2	±10.5	LSB
Conversion time	tconv	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin: ANI0 to ANI14, ANI16 to ANI20	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	3.1875		39	μs
			$1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	17		39	μs
			$1.6 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	57		95	μs
		10-bit resolution	$3.6 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	2.375		39	μs
		Target pin: internal reference voltage, and temperature sensor output voltage	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	3.5625		39	μs
	temperature sensor (HS (high-speed m		$2.4~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	$1.8 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$			±0.60	%FSR
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±0.85	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±0.85	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$			±4.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±6.5	LSB
Differential linearity error	DLE	10-bit resolution	$1.8 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$			±2.0	LSB
Note 1			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±2.5	LSB
Analog input voltage	Vain	ANI0 to ANI14		0		VDD	V
		ANI16 to ANI20		0		EVDD0	V
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) n	node)	V _{BGR} Note 4			V
		Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)			V _{TMPS25} Note 4		

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. When the conversion time is set to 57 μ s (min.) and 95 μ s (max.).

Note 4. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

(2) Interrupt & Reset Mode

(TA = -40 to +85°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Cond	litions	MIN.	TYP.	MAX.	Unit
Voltage detection	VLVDA0	VPOC2,	VPOC1, VPOC0 = 0, 0, 0, fa	lling reset voltage	1.60	1.63	1.66	V
threshold	VLVDA1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	VLVDA3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDB0	VPOC2,	VPOC1, VPOC0 = 0, 0, 1, fa	lling reset voltage	1.80	1.84	1.87	V
	VLVDB1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	VLVDB2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	VLVDB3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	VLVDC0	VPOC2, VPOC1, VPOC0 = 0, 1, 0, falling reset voltage				2.45	2.50	V
	VLVDC1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	VLVDC3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	VLVDD0	VPOC2,	VPOC1, VPOC0 = 0, 1, 1, fa	lling reset voltage	2.70	2.75	2.81	V
	VLVDD1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2	1	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	VLVDD3	1	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

2.6.7 Power supply voltage rising slope characteristics

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 2.4 AC Characteristics.

3.3 DC Characteristics

3.3.1 Pin characteristics

 $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le EVDD0 = EVDD1 \le VDD \le 5.5 \text{ V}, VSS = EVSS0 = EVSS1 = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147		2.4 V ≤ EVDD0 ≤ 5.5 V			-3.0 Note 2	mA
		P102, P120, P130, P140 to P145 2.7	4.0 V ≤ EVDD0 ≤ 5.5 V			-30.0	mA
			2.7 V ≤ EVDD0 < 4.0 V			-10.0	mA
	To P:		2.4 V ≤ EVDD0 < 2.7 V			-5.0	mA
		P30, P31, P50 to P57,	4.0 V ≤ EVDD0 ≤ 5.5 V			-30.0	mA
			2.7 V ≤ EVDD0 < 4.0 V			-19.0	mA
		P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147 (When duty ≤ 70% Note 3)	2.4 V ≤ EVDD0 < 2.7 V			-10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	2.4 V ≤ EVDD0 ≤ 5.5 V			-60.0	mA
	IOH2	Per pin for P20 to P27, P150 to P156	2.4 V ≤ VDD ≤ 5.5 V			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	2.4 V ≤ VDD ≤ 5.5 V			-1.5	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the EVDD0, EVDD1, VDD pins to an output pin.

Note 3. Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IoH × 0.7)/(n × 0.01) <Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins = (-10.0 × 0.7)/(80 × 0.01) ≈ -8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Note 2. Do not exceed the total current value.

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(5/5)

Items	Symbol	Conditi	ons		MIN.	TYP.	MAX.	Unit
Input leakage cur- rent, high	ILIH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Vi = EVDDO)			1	μΑ
	ILIH2	P20 to P27, P137, P150 to P156, RESET	VI = VDD				1	μΑ
	ILIH3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VDD	In input port or external clock input			1	μА
				In resonator con- nection			10	μА
Input leakage current, low	ILIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	VI = EVsso				-1	μΑ
	ILIL2	P20 to P27, P137, P150 to P156, RESET	Vı = Vss				-1	μА
	ILIL3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VSS	In input port or external clock input			-1	μА
				In resonator con- nection			-10	μА
On-chip pull-up resistance	Rυ	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	VI = EVsso	, In input port	10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Note 1. Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3. When high-speed system clock and subsystem clock are stopped.
- Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz to } 32 \text{ MHz}$

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1 MHz}$ to 16 MHz

- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
 Remark 3. fH: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is Ta = 25°C

<R><R>

<R><R>

<R>

(3) Flash ROM: 384 to 512 KB of 48- to 100-pin products

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operat-	HS (high-speed main)	fHOCO = 64 MHz,	Basic	V _{DD} = 5.0 V		2.9		mA
current Note 1		ing mode	mode Note 5	f _{IH} = 32 MHz Note 3	operation	V _{DD} = 3.0 V		2.9		
Note i				fHOCO = 32 MHz,	Basic	V _{DD} = 5.0 V		2.5		
				f _{IH} = 32 MHz Note 3	operation	V _{DD} = 3.0 V		2.5		
			HS (high-speed main)	fHOCO = 64 MHz,	Normal	V _{DD} = 5.0 V		6.0	11.2	mA
			mode Note 5	fih = 32 MHz Note 3	operation	V _{DD} = 3.0 V		6.0	11.2	
				fHOCO = 32 MHz,	Normal	V _{DD} = 5.0 V		5.5	10.6	
				fih = 32 MHz Note 3	operation	V _{DD} = 3.0 V		5.5	10.6	
				fHOCO = 48 MHz,	Normal	V _{DD} = 5.0 V		4.7	8.6	
				fih = 24 MHz Note 3	operation	V _{DD} = 3.0 V		4.7	8.6	
				fHOCO = 24 MHz,	Normal	V _{DD} = 5.0 V		4.4	8.2	
				fih = 24 MHz Note 3	operation	V _{DD} = 3.0 V		4.4	8.2	
				fHOCO = 16 MHz,	Normal	V _{DD} = 5.0 V		3.3	5.9	
		fin = 16 MHz Note 3	operation	V _{DD} = 3.0 V		3.3	5.9	•		
		HS (high-speed main)	f _{MX} = 20 MHz Note 2,	Normal	Square wave input		3.7	6.8	mA	
	mode Note 5	V _{DD} = 5.0 V	operation	Resonator connection		3.9	7.0			
		f _{MX} = 20 MHz Note 2,	Normal	Square wave input		3.7	6.8			
				V _{DD} = 3.0 V	operation	Resonator connection		3.9	7.0	
				f _{MX} = 10 MHz Note 2, V _{DD} = 5.0 V f _{MX} = 10 MHz Note 2, V _{DD} = 3.0 V	Normal	Square wave input		2.3	4.1	
					operation	Resonator connection		2.3	4.2	
					Normal operation	Square wave input		2.3	4.1	1
						Resonator connection		2.3	4.2	
			Subsystem clock	fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.2	7.7	μА
			operation	TA = -40°C	operation	Resonator connection		5.2	7.7	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.3	7.7	
				T _A = +25°C	operation	Resonator connection		5.3	7.7	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.5	10.6	
				T _A = +50°C	operation	Resonator connection		5.5	10.6	
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.9	13.2		
			T _A = +70°C	operation	Resonator connection		6.0	13.2		
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		6.8	17.5	•	
			T _A = +85°C	operation	Resonator connection		6.9	17.5	-	
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		15.5	77.8		
			T _A = +105°C	operation	Resonator connection		15.5	77.8		

(Notes and Remarks are listed on the next page.)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/2)

Parameter	Symbol	Conditions		HS (high-speed main) mode		Unit
				MIN.	MAX.	
Transfer rate		2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 k Ω , V_b = 2.7 V		2.6 Note 2	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$		Note 3	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 k Ω , V_b = 2.3 V		1.2 Note 4	Mbps
			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$		Note 5	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF, } R_b = 5.5 \text{ k}\Omega,$ $V_b = 1.6 \text{ V}$		0.43 Note 6	Mbps

Note 1. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $4.0~\text{V} \le \text{EV}_{\text{DD0}} \le 5.5~\text{V}$ and $2.7~\text{V} \le \text{V}_{\text{b}} \le 4.0~\text{V}$

Maximum transfer rate =
$$\frac{1}{ \{ -C_b \times R_b \times ln \ (1 - \frac{2.2}{V_b} \) \} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides
- Note 2. This value as an example is calculated when the conditions described in the "Conditions" column are met.

 Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- **Note 3.** The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EVDD0 < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{ \{ -C_b \times R_b \times \ln (1 - \frac{2.0}{V_b}) \} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln \left(1 - \frac{2.0}{V_b}\right)\}}{\left(\frac{1}{\text{Transfer rate}}\right) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides
- Note 4. This value as an example is calculated when the conditions described in the "Conditions" column are met.

 Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.



Note 5. The smaller maximum transfer rate derived by using fMck/12 or the following expression is the valid maximum transfer rate

Expression for calculating the transfer rate when 2.4 V \leq EVDD0 < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} }{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits} }$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides
- Note 6. This value as an example is calculated when the conditions described in the "Conditions" column are met.

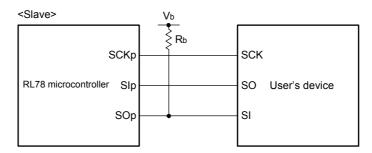
 Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin, and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)

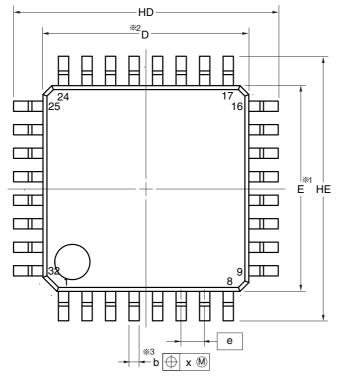


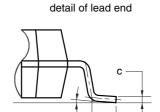
- Remark 1. R_b[Ω]: Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)
- Remark 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
- Remark 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

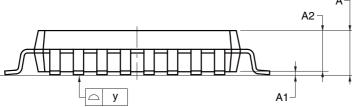
Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

R5F104BAAFP, R5F104BCAFP, R5F104BDAFP, R5F104BEAFP, R5F104BFAFP, R5F104BGAFP R5F104BADFP, R5F104BCDFP, R5F104BDDFP, R5F104BEDFP, R5F104BFDFP, R5F104BGDFP R5F104BAGFP, R5F104BCGFP, R5F104BDGFP, R5F104BEGFP, R5F104BFGFP, R5F104BGGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP32-7x7-0.80	PLQP0032GB-A	P32GA-80-GBT-1	0.2







(UNIT:mm)

	(-
ITEM	DIMENSIONS
D	7.00±0.10
Е	7.00±0.10
HD	9.00±0.20
HE	9.00±0.20
Α	1.70 MAX.
A1	0.10±0.10
A2	1.40
b	$0.37{\pm}0.05$
С	0.145 ± 0.055
L	0.50±0.20
θ	0° to 8°
е	0.80
х	0.20
v	0.10

NOTE

- 1. Dimensions "%1" and "%2" do not include mold flash.
- 2.Dimension "%3" does not include trim offset.

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